

What is claimed is:

1. A liquid crystal display device, comprising:
 - a gate electrode on a substrate;
 - a gate insulating film on the substrate and over the gate electrode;
 - a semiconductor layer on the gate insulating film and over the gate electrode;
 - a source electrode and a drain electrode on the semiconductor layer and adjacent the gate electrode, wherein the source electrode and the drain electrode each include at least one protrusion that extends toward the other electrode;
 - a protective layer on the gate insulating film and over the source and drain electrodes; and
 - a pixel electrode on the protective layer.
2. The liquid crystal display device as claimed in claim 1, wherein the semiconductor layer includes a "2"-shaped channel.
3. The liquid crystal display device as claimed in claim 1, wherein the semiconductor layer includes:
 - an active layer on the gate insulating film; and
 - an ohmic contact layer on the active layer.
4. The liquid crystal display device as claimed in claim 3, wherein the ohmic contact layer includes an "2"-shaped opening that corresponds to the shape of the channel.

16. The method as claimed in claim 13, wherein the ohmic contact layer is formed from doped silicon.

17. The method as claimed in claim 12, wherein the channel is formed with a length greater than 50 μm .

18. The method as claimed in claim 12, wherein the channel is formed only over the gate electrode.

19. The method as claimed in claim 11, wherein forming a protective layer includes forming an opening that exposes the drain electrode.

20. The method as claimed in claim 19, wherein forming a pixel electrode include forming the pixel electrode in electrical communication with the drain electrode.

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